## Obsolete (OPB821TXV)

## Features:

- Non-contact switching
- Low profile to facilitate stacking
- Hermetically sealed components
- $24^{\prime \prime}$ ( 609.60 mm ) minimum length wire conforms to MIL-W-16878
- TX components processed to MIL-PRF-19500



## Description:

Each OPB821TX device consists of a gallium aluminum arsenide LED and a silicon phototransistor, which are soldered into a printed circuit board and mounted in a high temperature plastic housing on opposite sides of an $0.080^{\prime \prime}$ ( 2.03 mm ) wide slot. Lead wires are \#24 AWG polytetraflouroethylene (PTFE) insulated, which conforms to MIL-W-16878.

Phototransistor switching takes place when an opaque object passes through the slot. For maximum output signal, neither the LED nor the phototransistor is apertured.

TX device components are processed to OPTEK's military screening program patterned after MIL-PRF-19500.
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.
Contact your local representative or OPTEK for more information.

## Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation

| Part <br> Number | LED <br> Peak <br> Wavelength | Sensor | Slot <br> Width / <br> Depth | $I_{\text {C(ON) }}$ <br> (mA) <br> Min |
| :---: | :---: | :---: | :---: | :---: |
| OPB821TX | 890 nm | Transistor | $0.080 " /$ <br> $0.255^{\prime \prime}$ | 0.80 |


| $I_{F}(m A)$ <br> Typ $/$ <br> Max | $\mathbf{V}_{\text {CE }}$ (Volts) <br> Max | A <br> E <br> M |
| :---: | :---: | :---: |
| $20 / 50$ | 30 | 0 |


| Aperture <br> Emitter/ <br> Sensor | Lead <br> Length / <br> Spacing |
| :---: | :---: |
| $0.040 " /$ | $24 " / 26$ |
| $0.040 "$ | AWG wire |

- Equipment safety
- Machine safety

| Color/Pin \# | Description | Color/Pin \# | Description |
| :---: | :---: | :---: | :---: |
| Green-3 | Cathode | White-2 | Collector |
| Orange-4 | Anode | Blue-1 | Emitter |



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Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Storage Temperature | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| :--- | ---: |
| Operating Temperature | $-65^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |
| Lead Soldering Temperature (1/16 inch $[1.6 \mathrm{~mm}]$ from case for 5 seconds with soldering iron) ${ }^{(1)}$ | $260^{\circ} \mathrm{C}$ |
| Input Diode |  |
| Continuous Forward Current | 50 mA |
| Reverse Voltage | 2 V |
| Power Dissipation ${ }^{(1)}$ | 100 mW |

Output Phototransistor

| Collector-Emitter Voltage | 50 V |
| :--- | ---: |
| Emitter-Collector Voltage | 7 V |
| Power Dissipation $^{(1)}$ | 100 mW |

Electrical Characteristics ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Input Diode |  |  |  |  |  |  |
| $V_{\text {F }}$ | Forward Voltage ${ }^{(3)}$ | 1.00 | 1.35 | 1.70 | V | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |
|  |  | 1.20 | 1.55 | 1.90 |  | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=-55^{\circ} \mathrm{C}$ |
|  |  | 0.80 | 1.20 | 1.60 |  | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C}$ |
| $I_{R}$ | Reverse Current | - | 0.10 | 100 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{R}}=2 \mathrm{~V}$ |

## Output Phototransistor

| $\mathrm{V}_{\text {(BR) }}$ ceo | Collector-Emitter Breakdown Voltage | 50 | 110 | - | V | $\mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}, \mathrm{I}_{\mathrm{F}}=0$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {(BR)ECO }}$ | Emitter-Collector Breakdown Voltage | 7 | 10 | - | V | $\mathrm{I}_{\mathrm{E}}=100 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{F}}=0$ |
| $I_{\text {c(0FF) }}$ | Collector-Emitter Dark Current | - | 0.20 | 100 | nA | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{l}_{\mathrm{F}}=0$ |
|  |  | - | 10 | 100 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=0, \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C}$ |
| Coupled |  |  |  |  |  |  |
| $I_{\text {con) }}$ | On-State Collector Current ${ }^{(3)}$ | 800 | - | - | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |
|  |  | 500 | - | - |  | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=-55^{\circ} \mathrm{C}$ |
|  |  | 500 | - | - |  | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}, \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{\text {CE(SAT) }}$ | Collector-Emitter Saturation Voltage | - | 0.20 | 0.30 | V | $\mathrm{I}_{\mathrm{C}}=250 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |

## TT Electronics

## Obsolete (OPB821TXV)

Electrical Characteristics ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Coupled |  |  |  |  |  |  |
| $\mathrm{t}_{\mathrm{r}}$ | Output Rise Time | - | 12 | 20 | $\mu \mathrm{s}$ | $\mathrm{V}_{\mathrm{CC}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}, \mathrm{R}_{\mathrm{L}}=1000 \Omega$ |
| $\mathrm{t}_{\mathrm{f}}$ | Output Fall Time | - | 12 | 20 |  |  |

Notes:
(1) Derate linearly $1.00 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $25^{\circ} \mathrm{C}$.
(2) Methanol or isopropanol are recommended cleaning agents.
(3) Measurement is taken during the last $500 \mu \mathrm{~s}$ of a single 1.0 ms test pulse. Heating due to increased pulse rate or pulse width can cause change in measurement results.





